FM0103/A

N-Channel Enhancement Mode Field Effect Transistor

- VDS: 100V
- ID: 3A
- RDS(ON)(at VGS=10V) ＜138 mohm
- RDS(ON)(at VGS=4.5V) ＜200 mohm

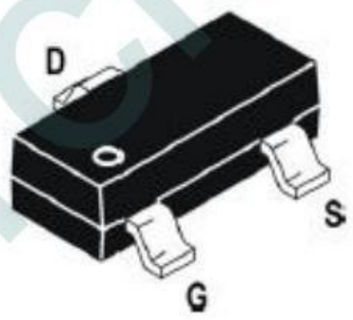
General Description

- Split Gate Trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low RDS(ON)
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Application

- Split Gate Trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low RDS(ON)
- Moisture Sensitivity Level 1
- Halogen Free

Package



SOT23-3

Absolute Maximum Ratings (Tc=25°Cunless otherwise specified)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		VDS	100	V
Gate-source Voltage		VGS	±20	V
Drain Current	TA=25°C	ID	3	A
	TA=70°C		2.4	
Pulsed Drain Current A		IDM	12	A
Avalanche energy B		EAS	7.9	mJ
Total Power Dissipation C	TA=25°C	PD	1.2	W
	TA=70°C		0.84	
Junction and Storage Temperature Range		TJ ,T STG	-55～ +150	℃

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